

## PROTONS TEST REPORT

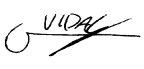


ESA study: "Survey of Critical Components for 150 kRad Power Systems"

ESTEC Contract N° 22831/09/NL/AF refers

<p><b>Part Type : SOC2222A</b></p> <p><b>Package : CCP-3</b></p> <p><b>Description : NPN Small Signal transistors</b></p> <p><b>Manufacturer: STMicroelectronics</b></p>
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Alter Technology Group Spain Purchase Order N° ATGSP-TL-09-JC-CO-9 dated 11/27/2009

Alter Technology Group Spain Project Manager: David NUNEZ

<b>Hirex reference :</b>	HRX/TID/0940	Issue : 01	Date :	June 03 <sup>rd</sup> , 2011
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Hirex Engineering	Protons Test Report		Ref.:	HRX/TID/0940
	SOC2222A	STMicroelectronics	Issue:	01

**PROTONS TEST REPORT**  
**on**  
**SOC2222A**  
**NPN Small Signal transistors**  
**From STMicroelectronics**

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## 1 Introduction

In the scope of the ESA study: "Survey of Critical Components for 150 kRad Power Systems", a protons test of the STMicroelectronics SOC2222A, NPN Small Signal transistors has been performed up to a total fluence of about  $2E11$  p/cm<sup>2</sup>, in response to Alter Technology Group Spain purchase order reference ATGSP-TL-09-JC-CO-9 that refers to ESTEC contract N° 22831/09/NL/AF.

Displacement damage effects were investigated using 60 MeV protons energy. Devices were irradiated at UCL in Louvain - Belgium.

The purpose of this test was to characterize degradation due to proton displacement damage so a further mission analysis could determine their suitability for flight use. This test was conducted on samples provided by Alter Technology Group Spain.

Test has been performed in accordance with Hirex Engineering Radiation Test Plan HRX/SPE/0225 issue 1 dated 04/19/2011.

A complete set of electrical measurements together with graphical representation of measured parameters with respect to Equivalent Fluence levels received is provided.

## 2 Applicable and Reference Documents

### 2.1 Applicable Documents

- Hirex Engineering Radiation Test Plan: HRX/SPE/0225 issue 2 dated 09/08/2011
- Alter Technology Group Proposal: ATGSP-OF-648/2009 Issue 1
- Minutes of Meeting: MM-SRP-ATG-0001 dated 29/10/2009
- Hirex specification: Total Ionizing dose test general procedure.
- ESCC detail specification: 5201-002

### 2.2 Reference Documents

- STMicroelectronics datasheet: Doc ID 16558 Rev 1, October 2009

## 3 Test Samples

7 samples of the SOC2222A devices were tested (6 + 1 control sample).

Allocation of samples used for testing is provided in the following table. Serial numbers were arbitrarily defined by Hirex.

Serial Number	Samples Allocation
1	Control sample
2	Biased OFF
3	Biased OFF
4	Biased OFF
5	Biased OFF
6	Biased OFF
7	Biased OFF

Identification of the SOC2222A is given below:

**Part Number:** SOC2222ASW

**Top Marking:** -

**Inspection lot:** DOC01283

**Date Code:** -

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## 4 Experimental Conditions

### 4.1 Radiation Source Description

The protons exposures were performed at the UCL facility in Louvain-la-Neuve - Belgium. The Proton Irradiation facility (Light Ion irradiation Facility or LIF) was used for this experiment. The corresponding experimental set-up is shown in Figure 1.

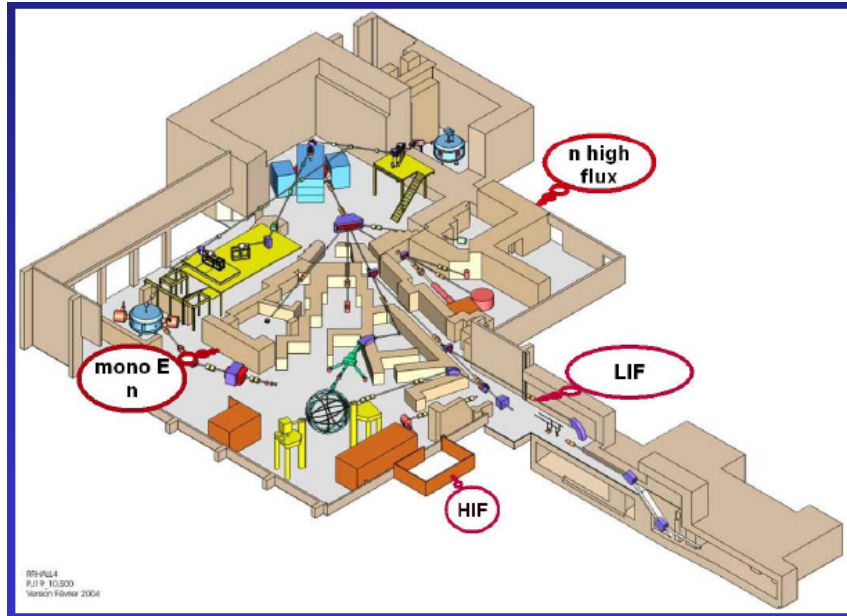


Figure 1 : LIF layout and typical experimental set-up

Light Ion irradiation Facility is characterized by the following beam parameters:

- Initial Proton Energies: 65 MeV;
- Energy Range: 9.3 – 62 MeV using energy degraders (See figure 2)
- Beam Flux at 62 MeV is between  $10^7$  p/cm<sup>2</sup>/sec to  $5 \times 10^8$  p/cm<sup>2</sup>/sec
- Irradiation Area: 8 cm diameter maximum

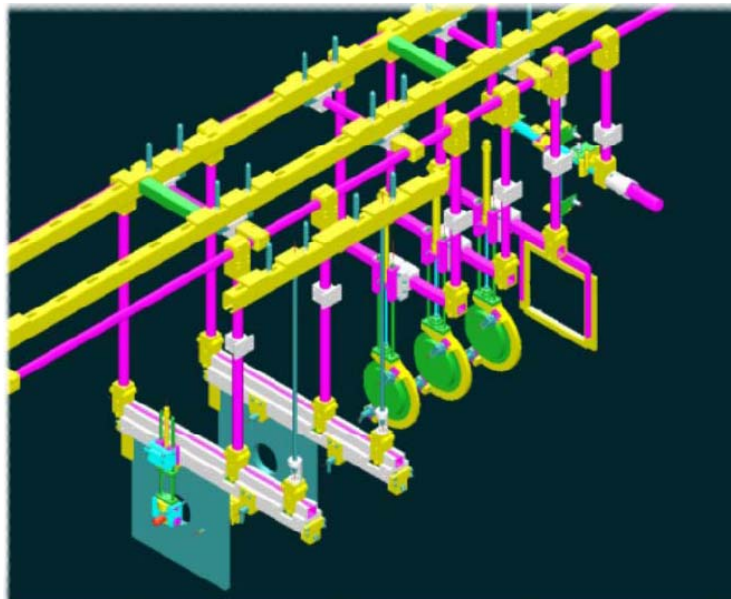


Figure 2: LIF Energy degraders

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The irradiation conditions used for this test are provided in the following tables:

Fluence Steps	Total Fluence	Flux	Equivalent Total Dose	T
p/cm <sup>2</sup> @60MeV	p/cm <sup>2</sup> @60MeV	p/cm <sup>2</sup> /s	Rad (Si)	°C
0	0		0	
2E+11	2E+11	5.00E+08	27.5E+3	25

## 4.2 Bias during Dose Exposures and Measurements conditions

### 4.2.1 Bias conditions

During exposures all samples were biased OFF with all pins connected to ground.

### 4.2.2 Electrical Measurements

Electrical parameters test program principle for SOC2222A is provided in Figure 3.

A HP4142 DC tester and a network analyzer HP8714ES were used to perform required measurements.

A dedicated test fixture and a test board were designed to ensure proper measurement conditions.

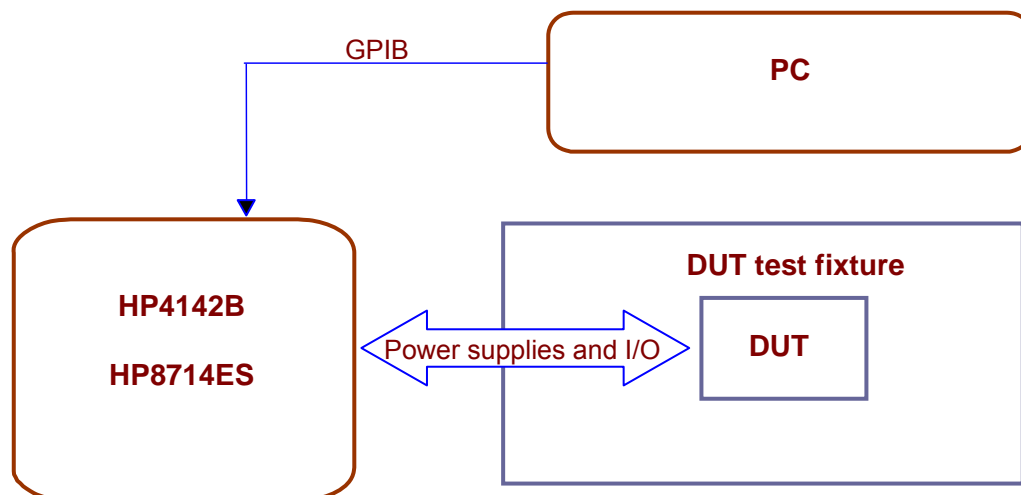


Figure 3 : SOC2222A test program principle

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Electrical parameters test conditions and limits used for performing this test are given in Table 1.

N°	Symbols	Characteristics	Test Conditions	Limits		Units
				Min	Max	
1	$I_{CBO}$	Collector-Base Cut-off Current	$V_{CB} = 60V$	-	10	nA
2	$I_{EBO}$	Emitter-Base Cut-off Current	$V_{EB} = 3V$	-	10	nA
3	$I_{CEO}$	Collector-Emitter Cut-off Current	$V_{CE} = 40V$		10	nA
4	$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu A$	75	-	V
5	$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 30mA$ , Note 1	40	-	V
6	$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\mu A$	6	-	V
7	$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage	$I_C = 150mA$ , $I_B = 15mA$ Note 1	-	0.3	V
8	$V_{BE(SAT)}$	Base-Emitter Saturation Voltage	$I_C = 150mA$ , $I_B = 15mA$ Note 1	-	1.2	V
9	$H_{FE1}$	Forward-Current Transfer Ratio	$I_C = 100\mu A$ , $V_{CE} = 10V$ Note 1	35	-	
10	$H_{FE2}$	Forward-Current Transfer Ratio	$I_C = 1mA$ , $V_{CE} = 10V$ Note 1	50	-	
11	$H_{FE3}$	Forward-Current Transfer Ratio	$I_C = 10mA$ , $V_{CE} = 10V$ Note 1	75		
12	$H_{FE4}$	Forward-Current Transfer Ratio	$I_C = 150mA$ , $V_{CE} = 10V$ Note 1	100	300	
13	$F_T$	Gain Bandwidth Product	$V_{CE}=20V$ , $I_C=20mA$	300	1000	MHz

Note 1 - Pulse measurement: Pulse Width  $\leq 300\mu s$ , duty cycle 1%.

**Table 1 : Measured electrical parameters**

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## 5 Conclusion

A proton displacement damage test was carried out by Hirex Engineering under Alter Technology Group Spain contract on the STMicroelectronics SOC2222A NPN Small Signal transistors in CCP-3 package.

Each device was exposed at room temperature to a protons flux of 60 MeV incident energy up to a total fluence of  $2E+11p/cm^2$ .

A summary of failed parameters is provided in the following table. Parameters not listed remained within specification limits all along testing. Detail test results are presented in the following section.

Parameters	Failure Level between :	Comments
<a href="#">ICEO</a>	0 & $2E+11p/cm^2$	

**Table 2 : Summary of parameters failure levels**



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## 6 Test Results

Test results including tables and graphics are provided in this section for each measured parameter.

Parameter measurements values are plotted versus Equivalent Fluence levels for 60 MeV incident energy protons. Fluences are expressed in protons/cm<sup>2</sup> in Silicon.

For each parameter, a drift calculation table is provided computing the drift between a given exposure step with respect to initial readings:

$$\Delta(\text{Parameter value}) = (\text{Parameter value}_{\text{POSTRAD}}) - (\text{Parameter value}_{\text{PRERAD}})$$

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Test conditions : PROTONS

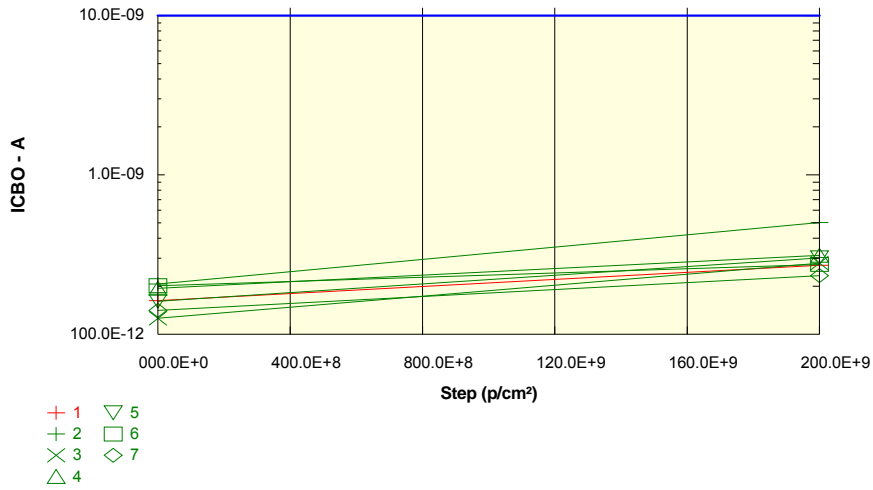
Parameter : Collector-Base cut-off current : ICBO

Vcb = 60V

Unit : A

Spec Limit Max : 10.0E-09

Spec limits are represented in bold lines on the graphic.



**Measurements**

ICBO	0 p/cm²	2E+11 p/cm²
1_REF	162.5E-12	270.4E-12
<b>OFF samples</b>		
2	206.6E-12	503.2E-12
3	126.0E-12	279.4E-12
4	194.2E-12	313.0E-12
5	160.9E-12	301.8E-12
6	201.8E-12	274.2E-12
7	141.2E-12	233.4E-12
<b>Statistics</b>		
Min	126.0E-12	233.4E-12
Max	206.6E-12	503.2E-12
Average	171.8E-12	317.5E-12
Sigma	31.0E-12	86.7E-12

**Drift Calculation**

ICBO	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
2	-	296.60E-12
3	-	153.40E-12
4	-	118.80E-12
5	-	140.90E-12
6	-	72.40E-12
7	-	92.20E-12
Average	-	145.72E-12
Sigma	-	72.81E-12

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Test conditions : PROTONS

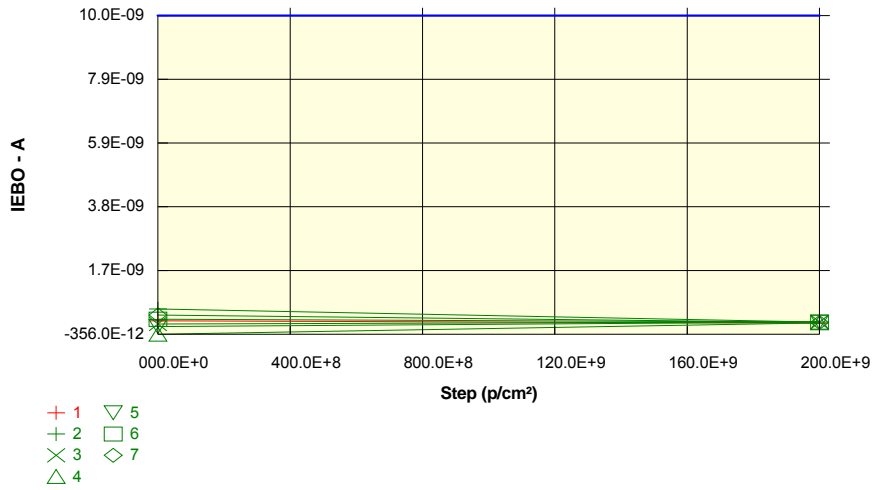
Parameter : Emitter-Base cut-off current : IEBO

V<sub>eb</sub> = 3V

Unit : A

Spec Limit Max : 10.0E-09

Spec limits are represented in bold lines on the graphic.



**Measurements**

IEBO	0 p/cm²	2E+11 p/cm²
1_REF	78.0E-12	3.0E-12
<b>OFF samples</b>		
2	466.0E-12	35.2E-12
3	-20.0E-12	44.2E-12
4	-356.0E-12	14.2E-12
5	-105.8E-12	40.1E-12
6	129.4E-12	34.6E-12
7	271.2E-12	26.3E-12
<b>Statistics</b>		
Min	-356.0E-12	14.2E-12
Max	466.0E-12	44.2E-12
Average	64.1E-12	32.4E-12
Sigma	264.9E-12	9.8E-12

**Drift Calculation**

IEBO	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
2	-	-430.80E-12
3	-	64.18E-12
4	-	370.24E-12
5	-	145.88E-12
6	-	-94.78E-12
7	-	-244.88E-12
Average	-	-31.69E-12
Sigma	-	261.72E-12

Test conditions : PROTONS

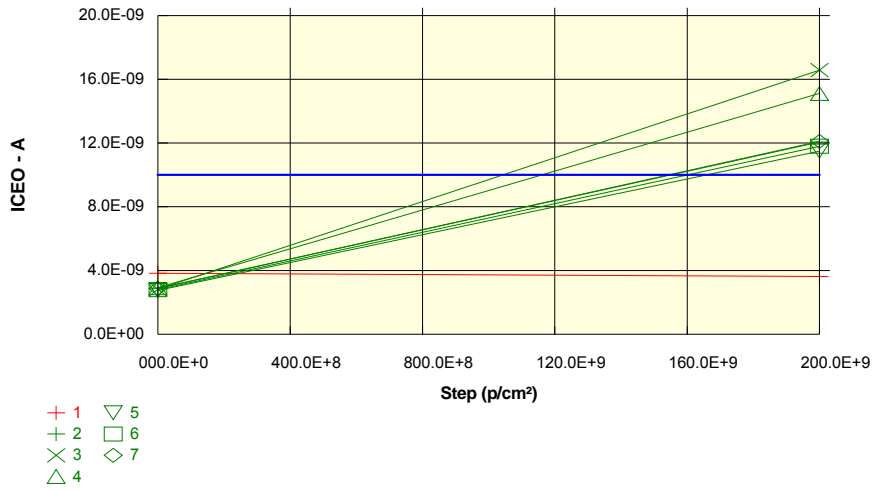
Parameter : Collector-Emitter cut-off current : ICEO

Vce = 40V

Unit : A

Spec Limit Max : 10.0E-09

Spec limits are represented in bold lines on the graphic.



Measurements

ICEO	0 p/cm²	2E+11 p/cm²
1 REF	3.8E-09	3.6E-09
OFF samples		
2	2.9E-09	12.1E-09
3	2.8E-09	16.6E-09
4	2.9E-09	15.1E-09
5	2.7E-09	11.5E-09
6	2.8E-09	11.8E-09
7	2.9E-09	12.1E-09
Statistics		
Min	2.7E-09	11.5E-09
Max	2.9E-09	16.6E-09
Average	2.8E-09	13.2E-09
Sigma	58.5E-12	1.9E-09

Drift Calculation

ICEO	0 p/cm²	2E+11 p/cm²
OFF samples		
2	-	9.17E-09
3	-	13.74E-09
4	-	12.20E-09
5	-	8.75E-09
6	-	9.00E-09
7	-	9.22E-09
Average	-	10.35E-09
Sigma	-	1.91E-09

Test conditions : PROTONS

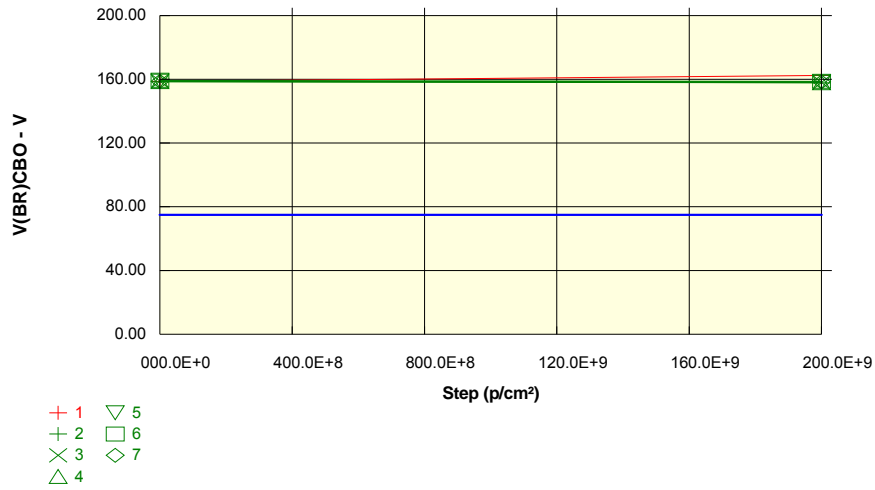
Parameter : Collector-Base breakdown voltage : V(BR)CBO

Ic = 100µA

Unit : V

Spec Limit Min : 75.00

Spec limits are represented in bold lines on the graphic.



**Measurements**

V(BR)CBO	0 p/cm²	2E+11 p/cm²
<b>1_REF</b>	158.80	162.39
<b>OFF samples</b>		
<b>2</b>	158.56	157.81
<b>3</b>	158.85	158.05
<b>4</b>	158.55	157.89
<b>5</b>	158.81	158.13
<b>6</b>	159.38	158.79
<b>7</b>	158.80	158.41
<b>Statistics</b>		
<b>Min</b>	158.55	157.81
<b>Max</b>	159.38	158.79
<b>Average</b>	158.83	158.18
<b>Sigma</b>	0.28	0.33

**Drift Calculation**

V(BR)CBO	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
<b>2</b>	-	-750.00E-03
<b>3</b>	-	-800.00E-03
<b>4</b>	-	-660.00E-03
<b>5</b>	-	-679.99E-03
<b>6</b>	-	-590.00E-03
<b>7</b>	-	-390.00E-03
<b>Average</b>	-	-645.00E-03
<b>Sigma</b>	-	132.00E-03

Test conditions : PROTONS

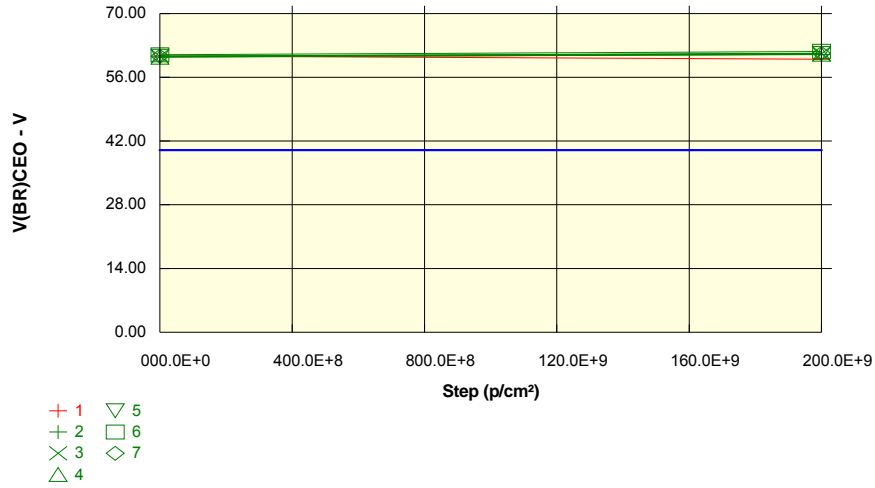
Parameter : Collector-Emitter breakdown voltage : V(BR)CEO

Ic = 30mA (pulse width 300µs)

Unit : V

Spec Limit Min : 40.00

Spec limits are represented in bold lines on the graphic.



**Measurements**

V(BR)CEO	0 p/cm²	2E+11 p/cm²
<b>1_REF</b>	60.67	59.99
<b>OFF samples</b>		
<b>2</b>	60.47	61.01
<b>3</b>	60.60	61.15
<b>4</b>	60.42	61.07
<b>5</b>	60.65	61.25
<b>6</b>	60.95	61.70
<b>7</b>	60.63	61.28
<b>Statistics</b>		
<b>Min</b>	60.42	61.01
<b>Max</b>	60.95	61.70
<b>Average</b>	60.62	61.24
<b>Sigma</b>	0.17	0.22

**Drift Calculation**

V(BR)CEO	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
<b>2</b>	-	540.00E-03
<b>3</b>	-	548.00E-03
<b>4</b>	-	650.00E-03
<b>5</b>	-	604.00E-03
<b>6</b>	-	752.00E-03
<b>7</b>	-	658.00E-03
<b>Average</b>	-	625.33E-03
<b>Sigma</b>	-	72.39E-03

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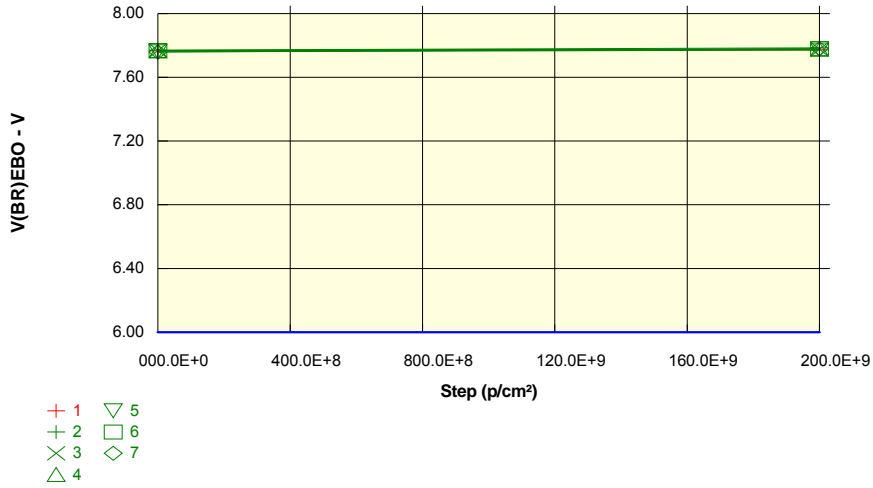
Parameter : Emitter-Base breakdown voltage : V(BR)EBO

Ie = 100µA

Unit : V

Spec Limit Min : 6.00

Spec limits are represented in bold lines on the graphic.



Measurements		
V(BR)EBO	0 p/cm²	2E+11 p/cm²
1_REF	7.77	7.77
OFF samples		
2	7.77	7.79
3	7.77	7.78
4	7.77	7.78
5	7.76	7.77
6	7.77	7.78
7	7.76	7.78
Statistics		
Min	7.76	7.77
Max	7.77	7.79
Average	7.77	7.78
Sigma	0.00	0.00

Drift Calculation		
V(BR)EBO	0 p/cm²	2E+11 p/cm²
OFF samples		
2	-	14.40E-03
3	-	7.60E-03
4	-	10.00E-03
5	-	11.20E-03
6	-	12.00E-03
7	-	20.80E-03
Average	-	12.67E-03
Sigma	-	4.17E-03

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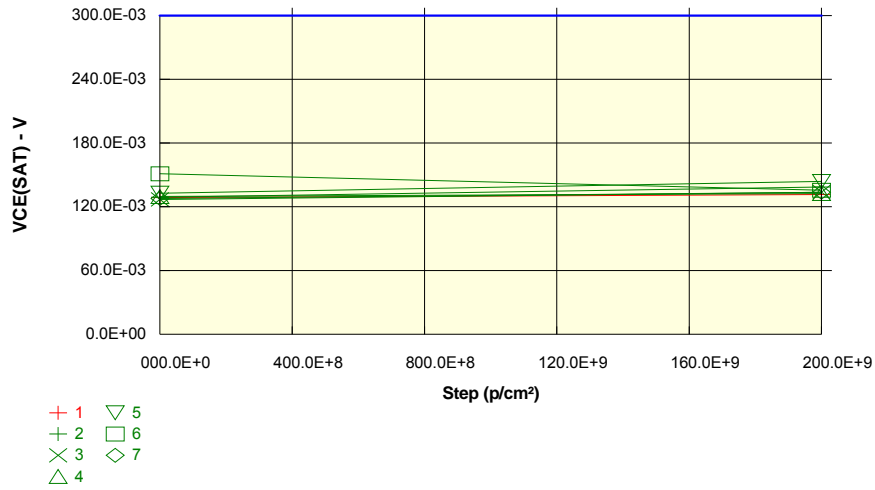
Parameter : Collector-Emitter saturation voltage : VCE(SAT)

Ic = 150mA ; ib = 15mA (pulse width 300µs)

Unit : V

Spec Limit Max : 300.0E-03

Spec limits are represented in bold lines on the graphic.



**Measurements**

VCE(SAT)	0 p/cm²	2E+11 p/cm²
<b>1_REF</b>	128.6E-03	131.6E-03
<b>OFF samples</b>		
2	129.0E-03	138.6E-03
3	126.9E-03	133.7E-03
4	129.6E-03	132.5E-03
5	132.8E-03	143.8E-03
6	151.0E-03	135.5E-03
7	127.8E-03	133.6E-03
<b>Statistics</b>		
Min	126.9E-03	132.5E-03
Max	151.0E-03	143.8E-03
Average	132.8E-03	136.3E-03
Sigma	8.3E-03	3.9E-03

**Drift Calculation**

VCE(SAT)	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
2	-	9.60E-03
3	-	6.84E-03
4	-	2.88E-03
5	-	11.04E-03
6	-	-15.48E-03
7	-	5.88E-03
Average	-	3.46E-03
Sigma	-	8.86E-03



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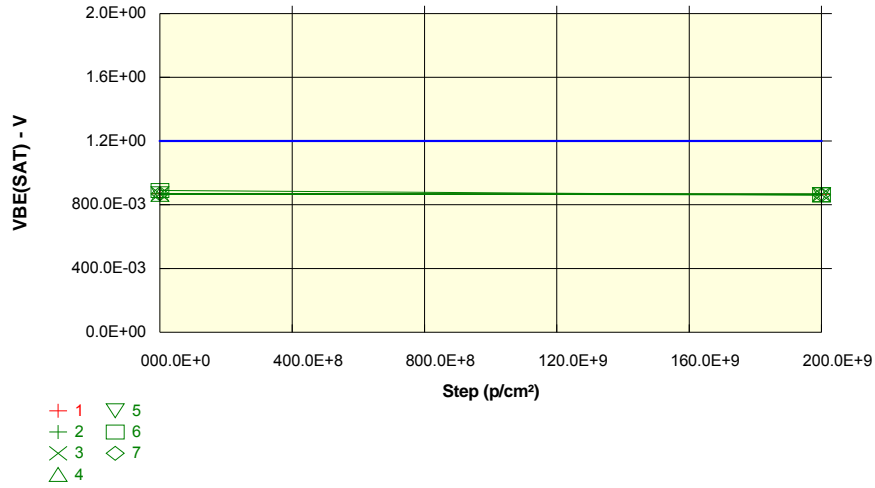
Parameter : Base-Emitter saturation voltage : VBE(SAT)

Ic = 150mA ; ib = 15mA (pulse width 300µs)

Unit : V

Spec Limit Max : 1.2E+00

Spec limits are represented in bold lines on the graphic.



**Measurements**

VBE(SAT)	0 p/cm²	2E+11 p/cm²
<b>1_REF</b>	869.8E-03	865.9E-03
<b>OFF samples</b>		
<b>2</b>	869.1E-03	869.2E-03
<b>3</b>	867.3E-03	865.1E-03
<b>4</b>	865.7E-03	863.4E-03
<b>5</b>	868.9E-03	864.8E-03
<b>6</b>	889.4E-03	861.6E-03
<b>7</b>	869.4E-03	862.7E-03
<b>Statistics</b>		
<b>Min</b>	865.7E-03	861.6E-03
<b>Max</b>	889.4E-03	869.2E-03
<b>Average</b>	871.6E-03	864.5E-03
<b>Sigma</b>	8.1E-03	2.4E-03

**Drift Calculation**

VBE(SAT)	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
<b>2</b>	-	79.99E-06
<b>3</b>	-	-2.20E-03
<b>4</b>	-	-2.32E-03
<b>5</b>	-	-4.12E-03
<b>6</b>	-	-27.88E-03
<b>7</b>	-	-6.64E-03
<b>Average</b>	-	-7.18E-03
<b>Sigma</b>	-	9.48E-03

**Test conditions : PROTONS**

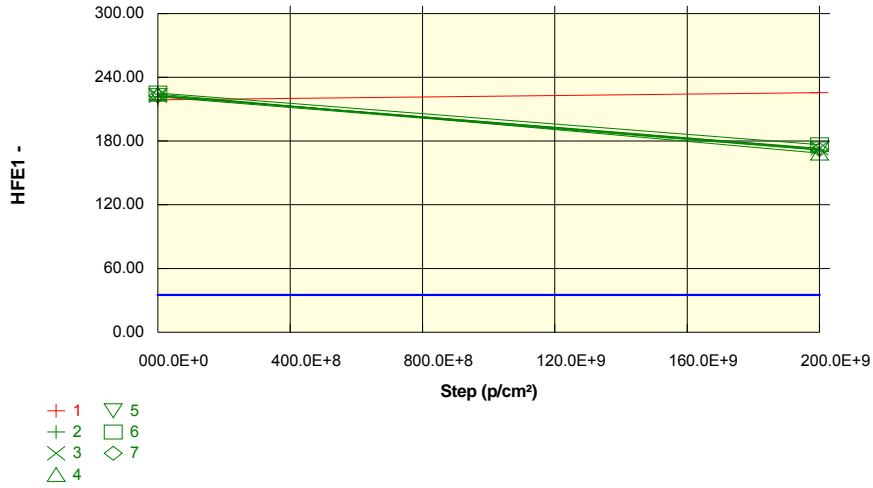
Parameter : Forward-Current Transfer Ratio : HFE1

Ic = 100µA ; Vce = 10V (pulse width 300µs)

Unit :

Spec Limit Min : 35.00

Spec limits are represented in bold lines on the graphic.



**Measurements**

HFE1	0 p/cm²	2E+11 p/cm²
1_REF	218.90	225.60
<b>OFF samples</b>		
2	221.63	171.43
3	222.83	173.09
4	224.22	168.67
5	222.80	172.64
6	225.20	176.60
7	222.53	171.99
<b>Statistics</b>		
Min	221.63	168.67
Max	225.20	176.60
Average	223.20	172.40
Sigma	1.17	2.35

**Drift Calculation**

HFE1	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
2	-	1.32E-03
3	-	1.29E-03
4	-	1.47E-03
5	-	1.30E-03
6	-	1.22E-03
7	-	1.32E-03
Average	-	1.32E-03
Sigma	-	74.12E-06

Hirex Engineering	Protons Test Report		Ref.:	HRX/TID/0940
	SOC2222A	STMicroelectronics	Issue:	01

Test conditions : PROTONS

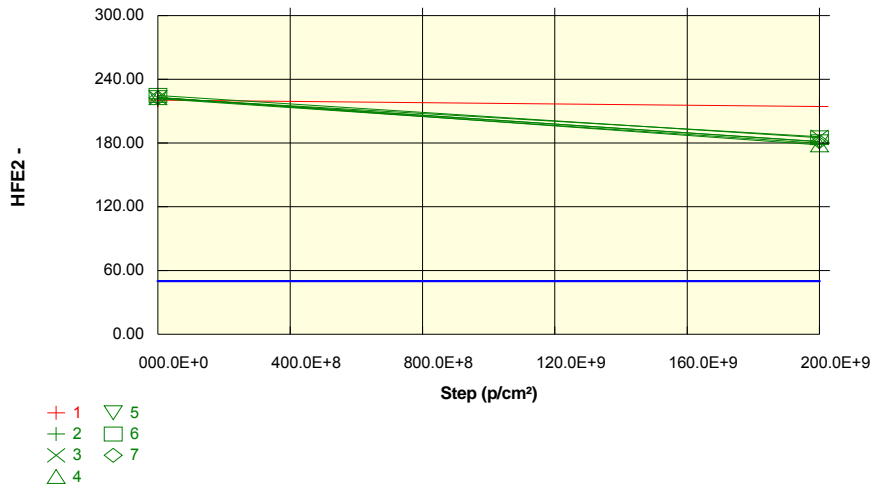
Parameter : Forward-Current Transfer Ratio : HFE2

Ic = 1mA ; Vce = 10V (pulse width 300µs)

Unit :

Spec Limit Min : 50.00

Spec limits are represented in bold lines on the graphic.



**Measurements**

HFE2	0 p/cm²	2E+11 p/cm²
1_REF	220.29	214.36
<b>OFF samples</b>		
2	221.68	179.62
3	222.40	185.93
4	222.87	178.29
5	222.77	181.29
6	224.88	185.08
7	222.54	181.37
<b>Statistics</b>		
Min	221.68	178.29
Max	224.88	185.93
Average	222.86	181.93
Sigma	0.98	2.75

**Drift Calculation**

HFE2	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
2	-	1.06E-03
3	-	881.97E-06
4	-	1.12E-03
5	-	1.03E-03
6	-	956.16E-06
7	-	1.02E-03
Average	-	1.01E-03
Sigma	-	75.65E-06

**Test conditions : PROTONS**

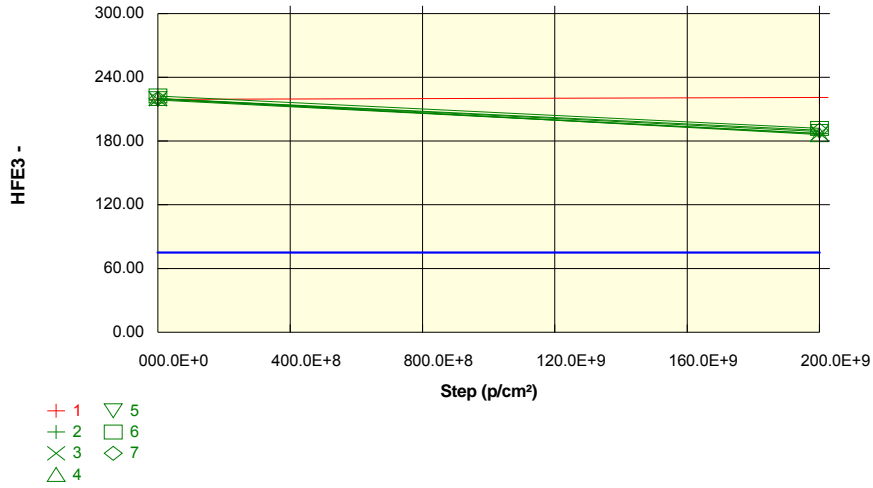
Parameter : Forward-Current Transfer Ratio : HFE3

Ic = 10mA ; Vce = 10V (pulse width 300µs)

Unit :

Spec Limit Min : 75.00

Spec limits are represented in bold lines on the graphic.



**Measurements**

HFE3	0 p/cm²	2E+11 p/cm²
1_REF	219.14	221.03
<b>OFF samples</b>		
2	218.72	186.94
3	219.33	187.17
4	219.95	186.03
5	219.82	188.99
6	222.41	191.95
7	220.07	190.20
<b>Statistics</b>		
Min	218.72	186.03
Max	222.41	191.95
Average	220.05	188.55
Sigma	1.15	2.05

**Drift Calculation**

HFE3	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
2	-	777.12E-06
3	-	783.49E-06
4	-	828.91E-06
5	-	742.04E-06
6	-	713.44E-06
7	-	713.42E-06
Average	-	759.74E-06
Sigma	-	41.34E-06

Hirex Engineering	Protons Test Report		Ref.:	HRX/TID/0940
	SOC2222A	STMicroelectronics	Issue:	01

Test conditions : PROTONS

Parameter : Forward-Current Transfer Ratio : HFE4

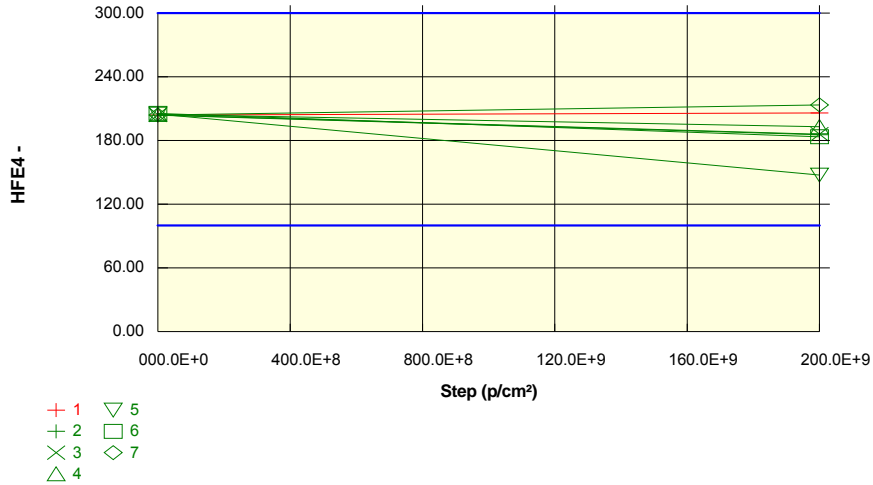
Ic = 150mA ; Vce = 10V (pulse width 300µs)

Unit :

Spec Limit Min : 100.00

Spec Limit Max : 300.00

Spec limits are represented in bold lines on the graphic.



Measurements		
HFE4	0 p/cm²	2E+11 p/cm²
1_REF	204.05	205.86
OFF samples		
2	203.90	185.31
3	204.08	185.82
4	204.48	193.04
5	204.80	147.36
6	205.52	183.54
7	203.95	213.47
Statistics		
Min	203.90	147.36
Max	205.52	213.47
Average	204.45	184.76
Sigma	0.57	19.56

Drift Calculation		
HFE4	0 p/cm²	2E+11 p/cm²
OFF samples		
2	-	491.79E-06
3	-	481.48E-06
4	-	289.99E-06
5	-	1.90E-03
6	-	582.85E-06
7	-	-218.71E-06
Average	-	588.44E-06
Sigma	-	644.23E-06

Test conditions : PROTONS

Parameter : Gain Bandwidth Product : FT

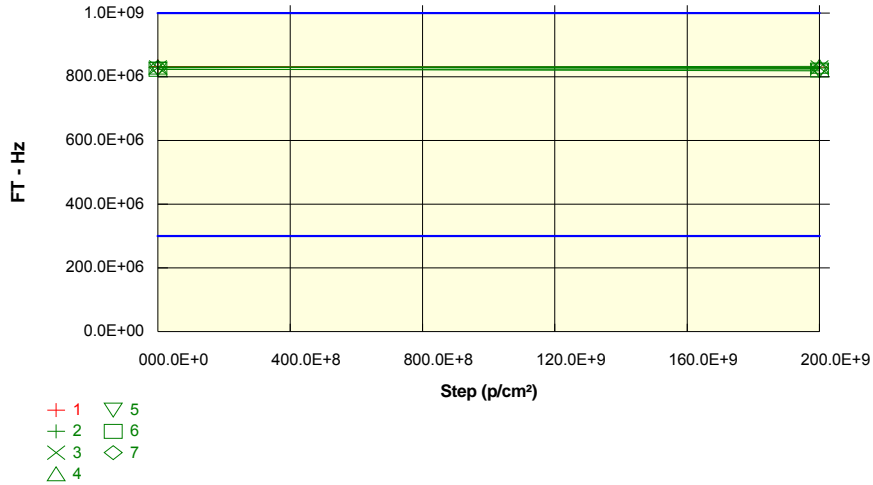
Vce = 20V ; Ic = 20mA

Unit : Hz

Spec Limit Min : 300.0E+06

Spec Limit Max : 1.0E+09

Spec limits are represented in bold lines on the graphic.



Measurements

FT	0 p/cm²	2E+11 p/cm²
1_REF	832.5E+06	830.2E+06
<b>OFF samples</b>		
2	829.5E+06	827.8E+06
3	829.3E+06	829.1E+06
4	830.6E+06	832.7E+06
5	824.3E+06	818.7E+06
6	823.2E+06	821.3E+06
7	829.7E+06	825.7E+06
<b>Statistics</b>		
Min	823.2E+06	818.7E+06
Max	830.6E+06	832.7E+06
Average	827.8E+06	825.9E+06
Sigma	2.9E+06	4.7E+06

Drift Calculation

FT	0 p/cm²	2E+11 p/cm²
<b>OFF samples</b>		
2	-	-1.72E+06
3	-	-190.98E+03
4	-	2.11E+06
5	-	-5.67E+06
6	-	-1.89E+06
7	-	-4.00E+06
Average	-	-1.90E+06
Sigma	-	2.51E+06